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High Frequency Design and Efficiency Optimization of LLC Resonant Converter Based on SiC Devices

Bingchi Chen

Changchun University of Technology, Changchun, China
20221209@stu.ccut.edu.cn

Abstract: With the rapid development of power electronics technology, the demand for power converters with high efficiency, high power density and high frequency response capability is increasing. In recent years, silicon carbide (SiC) devices have become a key material to meet this demand due to their excellent electrical characteristics. SiC devices not only operate stably at higher voltages and temperatures, but also have higher switching frequencies, making them ideal for high frequency and efficient power converter designs. LLC resonant converters are widely used in high power converters because of their high efficiency, soft switching characteristics and excellent voltage and current control performance. The introduction of SiC devices into the LLC resonant converter can not only improve the overall efficiency of the system, but also further reduce the volume and increase the power density under high frequency conditions. In this paper, the basic characteristics and advantages of SiC devices are analyzed, and the feasibility of their application in LLC resonant converters is described. Secondly, combined with high frequency conditions, the selection strategy of SiC devices is proposed, including voltage resistance, on-resistance, switching speed, thermal performance and other considerations. Finally, aiming at the application of SiC devices in LLC resonant converters, some efficiency optimization schemes are proposed to help improve the overall performance of the system.

Keywords: SiC device, LLC resonant converter, High frequency design, Efficiency optimization

1. Introduction

1.1. Research progress of LLC resonant converter

LLC resonant converters have become a prominent choice in high-efficiency power conversion due to their ability to achieve zero voltage switching (ZVS) and zero current switching (ZCS), which effectively reduce switching losses and electromagnetic interference (EMI) [1]. These converters are widely used in power supplies for telecommunications, industrial systems, and electric vehicles because they offer significant advantages over conventional hard-switching converters, including reduced switching losses, lower EMI, and increased power density [2].

The recent research in LLC resonant converters has focused on increasing operating frequency, reducing component size, lowering system costs, and improving system reliability. High-frequency operation is particularly beneficial as it allows for smaller magnetic components, leading to reduced size and weight, and enhanced power density. However, the challenge with high-frequency operation

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lies in the increased switching losses, which traditionally restrict the achievable frequencies in conventional silicon-based devices.

To address these limitations, the introduction of SiC (silicon carbide) devices has provided a significant breakthrough. SiC devices, particularly SiC MOSFETs [3], have superior switching characteristics, including higher switching speeds, lower switching losses, and higher temperature tolerance compared to traditional silicon devices. This makes them ideal for high-frequency LLC resonant converters, enabling higher switching frequencies without sacrificing efficiency. Researchers are also focusing on improving thermal management strategies, such as advanced cooling methods, to cope with the heat generated at higher frequencies and ensure the long-term reliability of the converter.

1.2. Application of SiC device in LLC resonant converter

SiC devices, especially SiC MOSFETs, offer several advantages that make them ideal for high-frequency LLC resonant converters. The key benefits of SiC devices include their ability to operate at higher voltages and frequencies, their low conduction losses, and their excellent high-temperature performance. SiC MOSFETs can handle much higher voltages than their silicon counterparts, and their lower on-resistance significantly reduces conduction losses. Additionally, SiC devices have a higher thermal conductivity, which allows for better heat dissipation, reducing the need for extensive cooling systems [4].

Incorporating SiC devices into LLC resonant converters enables several benefits, primarily through their impact on switching performance. SiC devices allow for higher switching frequencies, which leads to smaller passive components (inductors and capacitors) and thus a more compact system. This reduction in size and weight is particularly advantageous for applications in electric vehicles, renewable energy systems, and portable power supplies where space and weight are critical factors. Furthermore, the reduced switching losses in SiC devices help maintain high efficiency, even under high-frequency operation, making SiC-based LLC converters ideal for high-efficiency applications.

The fast switching speeds of SiC MOSFETs also contribute to reduced electromagnetic interference (EMI). High switching frequencies typically lead to higher EMI, which can interfere with other sensitive electronic systems. However, SiC devices mitigate this problem by reducing the rise and fall times of the switching transitions, thus lowering EMI levels and ensuring compliance with electromagnetic compatibility (EMC) standards.

Another major advantage of SiC-based LLC converters is improved thermal performance. SiC's high thermal conductivity and low on-resistance help dissipate heat more effectively, which is crucial in high-frequency, high-power applications. As a result, SiC-based converters can operate at higher power levels without the need for complex cooling solutions, which reduces system complexity and cost.

In conclusion, the application of SiC devices in LLC resonant converters provides significant improvements in efficiency, size, weight, and thermal management, making them a superior choice for high-frequency power conversion. Their ability to operate at higher frequencies with lower switching losses positions SiC-based LLC converters as a key technology for future high-efficiency, high-power density power supplies, especially in the fields of renewable energy, electric vehicles, and industrial applications.

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2. The advantages of SiC devices combined with the LLC resonant converter design

2.1. Basic characteristics and advantages of SiC devices

SiC, as a wide bandgap semiconductor material, has many properties that are superior to traditional silicon devices, which give it great advantages in high power, high frequency and high temperature applications [5]. SiC has a bandgap width of 3.26 eV, which is three times that of silicon, so SiC can withstand higher electric field strength, and its breakdown electric field strength is 10 times that of silicon. This allows SiC devices to operate stably at higher voltages, with better radiation resistance and increased reliability. In addition, the thermal conductivity of SiC is about three times that of silicon, allowing SiC devices to operate stably under high power, high temperature conditions, reducing the requirements for thermal design. SiC devices also switch faster and can switch at higher frequencies, reducing switching losses.

In addition to the above advantages, SiC devices also perform well in terms of resistance to electromagnetic interference and voltage sudden changes. Due to its higher breakdown voltage and high temperature resistance, SiC devices are able to maintain a stable operating state in harsh environments, even in the case of high voltage fluctuations or rapid changes, and can avoid failures caused by overvoltage or overheating. This makes SiC materials ideal for applications that require high reliability, such as aerospace, military equipment, and automotive electronics.

2.2. Application advantages of SiC devices in LLC resonant converters

The high efficiency and soft switching characteristics of the LLC resonant converter make it an important structure in power conversion, especially in high-power applications where energy efficiency and compactness are critical. The introduction of SiC devices significantly enhances the performance of the LLC converter. First, the high switching frequency of SiC devices allows LLC converters to operate at elevated frequencies, which reduces the size of magnetic components and increases overall power density, making the system more compact. Second, the low switching losses of SiC devices ensure that the converter maintains high efficiency even at these high operating frequencies, thus minimizing energy loss. Additionally, the high temperature operating capability of SiC devices improves thermal stability in LLC converters, reducing the need for complex and costly thermal management systems, which leads to a more robust and reliable converter design. This combination of features makes SiC-enhanced LLC converters highly suitable for demanding applications, including renewable energy systems and electric vehicles.

2.3. Challenges and countermeasures in SiC device application

Despite the many advantages of SiC devices, there are still some challenges in their application, mainly reflected in the following aspects:

a. High cost: The manufacturing cost of SiC devices is high, especially in some cost-sensitive applications, which may face cost effectiveness challenges. However, as SiC manufacturing technology continues to mature and scale production, it is expected that its cost will gradually decrease.

b. High drive requirements: the drive voltage and drive current requirements of SiC devices are high, especially in high-frequency operation, and the design of the drive circuit needs to be optimized according to the characteristics of SiC devices.

c. Optimization of switching frequency and resonance design: under high frequency conditions, how to reasonably select resonant inductors and capacitors, optimize switching frequency and system stability, is still a key issue in the design of LLC converter.

In response to these challenges, the researchers have proposed some optimization schemes, including optimizing the drive circuit, reducing the cost of technical solutions, and efficient thermal management design, which will be introduced in the following sections.

3. SiC device selection and system optimization under high frequency operating conditions

3.1. SiC device selection

In high frequency applications, the choice of SiC devices is critical. First, it is necessary to select the appropriate voltage level of the SiC device based on the input and output voltage of the LLC converter. SiC MOSFETs typically have a high voltage resistance and are suitable for high voltage applications. Secondly, on-resistance is an important parameter that affects the efficiency of SiC devices, and lower on-resistance can effectively reduce on-loss. Switching speed is another important selection criterion. SiC devices switch faster, but it is necessary to ensure that they can maintain good switching performance at high frequency conditions. Thermal performance is also a factor to consider when selecting SiC devices, and a sound thermal management design helps to ensure that devices can operate stably at high power outputs.

In addition to voltage levels, on-resistance, switching speed, and thermal performance, the selection of SiC devices should also consider their package type and drive characteristics. In high frequency applications, the packaging form of SiC devices has a significant impact on their thermal performance, reliability and electrical performance. For example, package designs with low parasitic inductors and capacitors can reduce losses when switching at high frequencies and improve overall system efficiency. Proper packaging also enhances the thermal resistance and electrical stability of the device under high temperature and pressure conditions.

3.2. LLC Converter efficiency optimization scheme

Optimization of resonant circuit design: By choosing resonant inductors and capacitors properly, it is possible to ensure that the LLC converter can achieve zero voltage on (ZVS) and zero current off (ZCS) at high frequencies, thereby reducing switching losses, as shown in formula (1).

$$f_{res} = \frac{1}{2\pi\sqrt{L_r C_r}} \tag{1}$$

Where, L_r and C_r are resonant inductors and capacitors respectively, and f_{res} is the resonant frequency.

Improved magnetic component design: The use of low-loss magnetic materials can reduce core losses and copper losses, especially in high-frequency applications, optimizing the design of magnetic components is critical [6].

Optimize PCB layout: Reduce parasitic inductors and capacitors, and improve system stability and efficiency by optimizing PCB layout and routing, reducing electromagnetic interference (EMI) problems.

Adopting synchronous rectification technology: the introduction of synchronous rectification technology can effectively reduce the rectification loss and improve the conversion efficiency. Synchronous rectifier devices can operate at high frequencies with low switching losses.

3.3. Thermal management and thermal optimization

Since SiC devices generate higher heat when operating at high frequencies and high power, effective thermal management design is key to ensuring their reliability [7]. Thermal management performance can be improved by selecting a package with low thermal resistance, optimizing thermal design, and

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using materials with high thermal conductivity. Especially in high-power and high-frequency applications, the heat dissipation problem is more important, so efficient heat dissipation solutions should be used, such as increasing heat sinks, using liquid cooling systems, etc.

3.4. Computational efficiency optimization and system simulation

In order to evaluate the effectiveness of system efficiency optimization, pre-design and analysis are often carried out through system simulation. Through simulation, the optimal operating frequency, resonant element value, and SiC device operating characteristics can be determined to achieve maximum efficiency.

In simulation, efficiency expressions can be calculated to help evaluate the overall performance of the system. For example, as shown in formula (2).

$$\eta = \frac{P_{out}}{P_{in}} \times 100\% \qquad (2)$$

Where, P_{out} is the output power and P_{in} is the input power. The goal of efficiency optimization is to minimize losses and improve overall efficiency by adjusting design parameters, selecting appropriate SiC devices, and optimizing factors such as drive circuits and thermal management [8].

4. Conclusion and summary

By analyzing the basic characteristics of SiC device and its application in LLC resonant converter, this paper proposes a high frequency design and efficiency optimization scheme based on SiC device. By introducing SiC devices into the LLC resonant converter, the switching frequency of the system can be effectively increased, the switching loss can be reduced, and the thermal performance of the system can be improved, thereby increasing the overall efficiency and power density. The soft switching characteristics of the LLC resonant converter complement the high switching frequency and low loss characteristics of the SiC device, enabling efficient operation at higher frequencies and reducing the size of the magnetic component, thereby increasing the power density. This provides a more competitive solution for high-frequency, high-power applications.

With the growing global demand for energy efficient and environmentally friendly technologies, the power electronics industry is facing increasing challenges. Traditional silicon-based devices have gradually exposed performance bottlenecks in application scenarios such as high frequency, high temperature and high power density, and SiC devices have become one of the key technologies to address these challenges due to their superior physical characteristics. As an efficient power converter, LLC resonant converter has been widely used in many industrial applications. In terms of high-frequency design, the introduction of SiC devices has brought significant performance improvements to LLC converters, especially in terms of switching frequency, efficiency and power density. The high frequency switching characteristics of SiC devices can effectively reduce the volume of the converter, especially in applications requiring miniaturization design, SiC devices show great potential. In addition, the low on-resistance and low switching loss characteristics of SiC devices can significantly improve the efficiency of the converter and reduce the heat dissipation requirements of the system.

Although the performance of SiC devices at high frequencies and high temperatures is superior, there are still some challenges in terms of cost, drive design and manufacturing process. Currently, the high cost of SiC devices is an important factor limiting their wide application, especially in low - and medium-power and low-cost applications. However, with the continuous development of SiC technology and the expansion of manufacturing scale, the cost of SiC devices is expected to gradually decrease, which will further promote its application in a wider range of fields.

In the future, with the increasing demand for efficient and high-density power supplies in areas such as electric vehicles, renewable energy and smart grids, SiC devices will be more widely used in power electronics. Especially in the chargers, inverters and on-board power supplies of electric vehicles, the advantages of SiC devices will be fully utilized. With the further improvement of the manufacturing process, the application of SiC devices will not be limited to high-end applications, but will also penetrate into more consumer electronics and home appliances.

In terms of technology development, future research can further promote the application of SiC devices from multiple perspectives: First, there is still a lot of room for optimization in the packaging and heat dissipation design of SiC devices, especially under high frequency and high power conditions, how to effectively reduce heat loss and improve the thermal management capability of devices will be the key to improve the performance of SiC devices. Secondly, optimization of SiC device driver circuit will also be an important research direction in the future, to solve its special requirements for the driver circuit in high-frequency applications, to ensure that the device can maintain stability under the conditions of high-speed switching. In addition, for the overall system integration of SiC devices and LLC resonant converters, further optimization and simulation analysis will help improve the efficiency and reliability of the system.

In summary, LLC resonant converters based on SiC devices have significant advantages in high frequency, high power and high efficiency applications. Although the current cost, drive design and other aspects still face challenges, but with the progress of technology, SiC devices will play an increasingly important role in the field of power electronics, especially in the field of high-frequency power supply, green energy and smart grid, SiC devices have a broad application prospect. In the future, the combination of SiC devices and LLC resonant converters will promote the development of power conversion technology in a more efficient, smaller and more intelligent direction, making an important contribution to achieving global energy conservation and green environmental protection goals.

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